2-input AND gate Rev. 04 — 17 July 2007

### 1. General description

74HC1G08 and 74HCT1G08 are high-speed, Si-gate CMOS devices. They provide a 2-input AND function.

The HC device has CMOS input switching levels and supply voltage range 2 V to 6 V.

The HCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

The standard output currents are half those of the 74HC08 and 74HCT08.

### 2. Features

- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- SOT353-1 and SOT753 package options

## 3. Ordering information

#### Table 1.Ordering information

Type number	Package						
	Temperature range	Name	Description	Version			
74HC1G08GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads;	SOT353-1			
74HCT1G08GW			body width 1.25 mm				
74HC1G08GV	–40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753			
74HCT1G08GV							

### 4. Marking

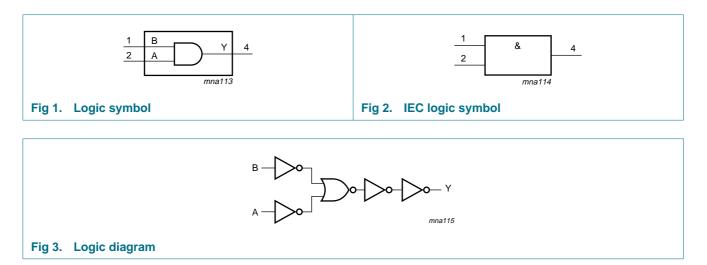
#### Table 2.Marking codes

Type number	Marking
74HC1G08GW	HE
74HCT1G08GW	TE
74HC1G08GV	H08
74HCT1G08GV	T08



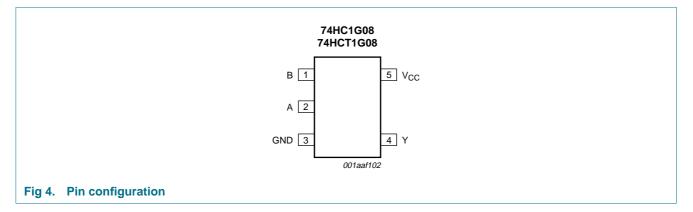
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# 5. Functional diagram



## 6. Pinning information

### 6.1 Pinning



### 6.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
В	1	data input
А	2	data input
GND	3	ground (0 V)
Y	4	data output
V <sub>CC</sub>	5	supply voltage

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# 7. Functional description

#### Table 4.Function table

*H* = *HIGH* voltage level; *L* = *LOW* voltage level

Input		Output
Α	В	Y
L	L	L
L	Н	L
Н	L	L
Н	Н	Н

### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V). [1]

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+7.0	V
I <sub>IK</sub>	input clamping current	$V_{\rm I}$ < -0.5 V or $V_{\rm I}$ > $V_{\rm CC}$ + 0.5 V	-	±20	mA
I <sub>OK</sub>	output clamping current	$V_{\rm O}$ < –0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V	-	±20	mA
I <sub>O</sub>	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±12.5	mA
I <sub>CC</sub>	supply current		-	25	mA
I <sub>GND</sub>	ground current		-25	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \text{ to } +125 \ ^{\circ}C$	[2] _	200	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] Above 55 °C the value of  $\mathsf{P}_{tot}$  derates linearly with 2.5 mW/K.

## 9. Recommended operating conditions

#### Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74HC1G08			74HCT1G08			Unit
			Min	Тур	Max	Min	Тур	Max	
V <sub>CC</sub>	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	$V_{CC}$	0	-	$V_{CC}$	V
Vo	output voltage		0	-	V <sub>CC</sub>	0	-	V <sub>CC</sub>	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	-40	+25	+125	°C
	input transition rise	$V_{CC} = 2.0 V$	-	-	625	-	-	-	ns/V
	and fall rate	$V_{CC} = 4.5 V$	-	-	139	-	-	139	ns/V
		$V_{CC} = 6.0 V$	-	-	83	-	-	-	ns/V

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# **10. Static characteristics**

#### Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V). All typical values are measured at  $T_{amb}$  = 25 °C.

Symbol	Parameter	Conditions	-40	°C to +8	85 °C	<b>−40</b> °C	Unit	
			Min	Тур	Max	Min	Max	
For type	74HC1G08							·
V <sub>IH</sub>	HIGH-level input	$V_{CC} = 2.0 V$	1.5	1.2	-	1.5	-	V
	voltage	$V_{CC} = 4.5 V$	3.15	2.4	-	3.15	-	V
		V <sub>CC</sub> = 6.0 V	4.2	3.2	-	4.2	-	V
V <sub>IL</sub>	LOW-level input	$V_{CC} = 2.0 V$	-	0.8	0.5	-	0.5	V
	voltage	$V_{CC} = 4.5 V$	-	2.1	1.35	-	1.35	V
		$V_{CC} = 6.0 V$	-	2.8	1.8	-	1.8	V
V <sub>OH</sub>	HIGH-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$						
voltage	voltage	$I_{O} = -20 \ \mu A; \ V_{CC} = 2.0 \ V$	1.9	2.0	-	1.9	-	V
		$I_O$ = –20 $\mu\text{A};V_{CC}$ = 4.5 V	4.4	4.5	-	4.4	-	V
		$I_{O} = -20 \ \mu A; \ V_{CC} = 6.0 \ V$	5.9	6.0	-	5.9	-	V
		$I_{O} = -2.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	4.13	4.32	-	3.7	-	V
		$I_{O} = -2.6 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.63	5.81	-	5.2	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$						
		$I_{O} = 20 \ \mu A; \ V_{CC} = 2.0 \ V$	-	0	0.1	-	0.1	V
		$I_0 = 20 \ \mu A; \ V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	V
		$I_0 = 20 \ \mu A; \ V_{CC} = 6.0 \ V$	-	0	0.1	-	0.1	V
		$I_{O}$ = 2.0 mA; $V_{CC}$ = 4.5 V	-	0.15	0.33	-	0.4	V
		$I_{O} = 2.6 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.33	-	0.4	V
l <sub>i</sub>	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0$ V	-	-	1.0	-	1.0	μΑ
lcc	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0$ V	-	-	10	-	20	μΑ
Cı	input capacitance		-	1.5	-	-	-	pF
For type	74HCT1G08							
V <sub>IH</sub>	HIGH-level input voltage	$V_{CC}$ = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	V
VIL	LOW-level input voltage	$V_{CC}$ = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	V
V <sub>он</sub>	HIGH-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$						
	voltage	$I_{O} = -20 \ \mu A; \ V_{CC} = 4.5 \ V$	4.4	4.5	-	4.4	-	V
		$I_{O}$ = -2.0 mA; $V_{CC}$ = 4.5 V	4.13	4.32	-	3.7	-	V
V <sub>OL</sub>	LOW-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$						
	voltage	$I_{O}$ = 20 µA; $V_{CC}$ = 4.5 V	-	0	0.1	-	0.1	V
		$I_{O}$ = 2.0 mA; $V_{CC}$ = 4.5 V	-	0.15	0.33	-	0.4	V
1	input leakage current	$V_{I} = V_{CC}$ or GND; $V_{CC} = 5.5 V$	-	-	1.0	-	1.0	μA

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Voltages a	/oltages are referenced to GND (ground = 0 V). All typical values are measured at $T_{amb}$ = 25 °C.							
Symbol	Parameter	Conditions	–40 °C to +85 °C			_40 °C t	Unit	
			Min	Тур	Max	Min	Max	
I <sub>CC</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	10	-	20	μA
$\Delta I_{CC}$	additional supply current	per input; V <sub>CC</sub> = 4.5 V to 5.5 V; V <sub>I</sub> = V <sub>CC</sub> - 2.1 V; I <sub>O</sub> = 0 A	-	-	500	-	850	μΑ
CI	input capacitance		-	1.5	-	-	-	pF

#### Table 7. Static characteristics ... continued

## **11. Dynamic characteristics**

#### Table 8. Dynamic characteristics

GND = 0 V;  $t_r = t_f \le 6.0$  ns; All typical values are measured at  $T_{amb} = 25 \degree C$ . For test circuit see Figure 6

Symbol	Parameter	Conditions		<b>−40 °C to +85 °C</b>			_40 °C t	Unit	
				Min	Тур	Max	Min	Max	
For type	74HC1G08								
t <sub>pd</sub>	propagation delay	A and B to Y; see Figure 5	<u>[1]</u>						
		$V_{CC} = 2.0 \text{ V}; \text{ C}_{L} = 50 \text{ pF}$		-	25	115	-	135	ns
		$V_{CC} = 4.5 \text{ V}; \text{ C}_{L} = 50 \text{ pF}$		-	9	23	-	27	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	7	-	-	-	ns
		$V_{CC} = 6.0 \text{ V}; C_{L} = 50 \text{ pF}$		-	8	20	-	23	ns
C <sub>PD</sub>	power dissipation capacitance	$V_I = GND$ to $V_{CC}$	[2]	-	19	-	-	-	pF
For type	74HCT1G08								
t <sub>pd</sub>	propagation delay	A and B to Y; see Figure 5	<u>[1]</u>						
		$V_{CC} = 4.5 \text{ V}; \text{ C}_{L} = 50 \text{ pF}$		-	11	23	-	27	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	11	-	-	-	ns
C <sub>PD</sub>	power dissipation capacitance	$V_{I}$ = GND to $V_{CC}$ – 1.5 V	[2]	-	21	-	-	-	pF

[1]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

[2]  $C_{PD}$  is used to determine the dynamic power dissipation  $P_D$  ( $\mu$ W).

$$\begin{split} P_{D} &= C_{PD} \times V_{CC}^{2} \times f_{i} + \Sigma \; (C_{L} \times V_{CC}^{2} \times f_{o}) \; \text{where:} \\ f_{i} &= \text{input frequency in MHz} \\ f_{o} &= \text{output frequency in MHz} \end{split}$$

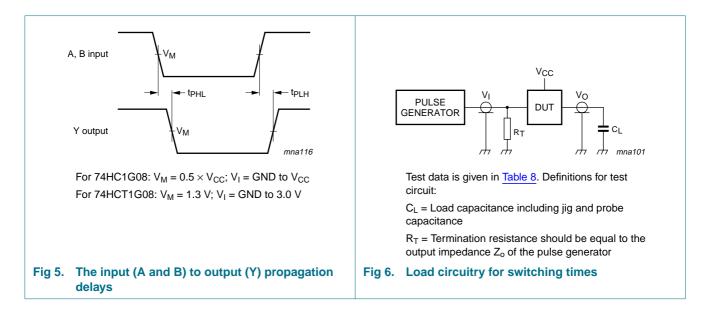
 $C_{\text{L}}$  = output load capacitance in pF

 $V_{CC}$  = supply voltage in Volts

 $\Sigma~(C_L \times V_{CC}{}^2 \times f_o)$  = sum of outputs

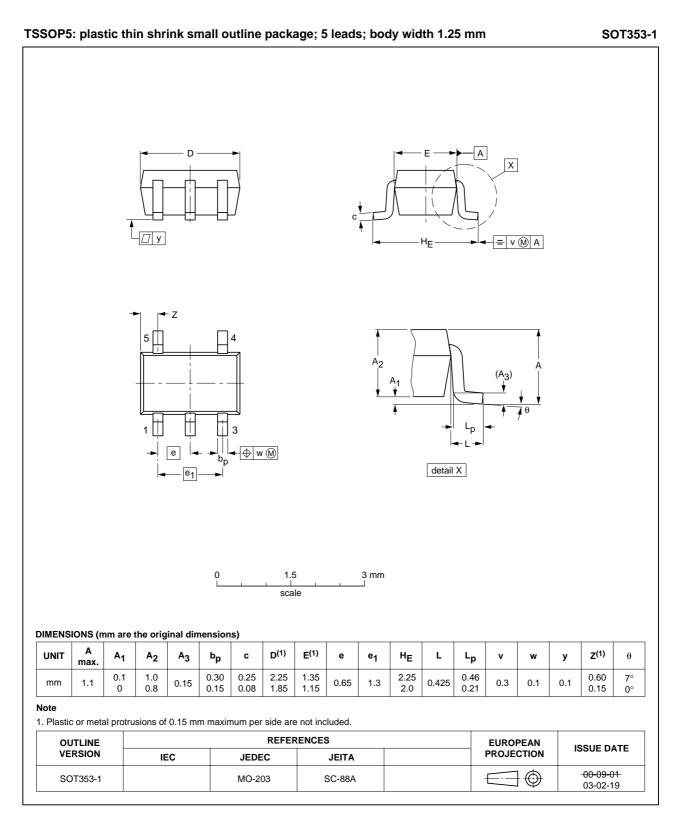
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# 12. Waveforms



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## 13. Package outline



#### Fig 7. Package outline SOT353-1 (TSSOP5)

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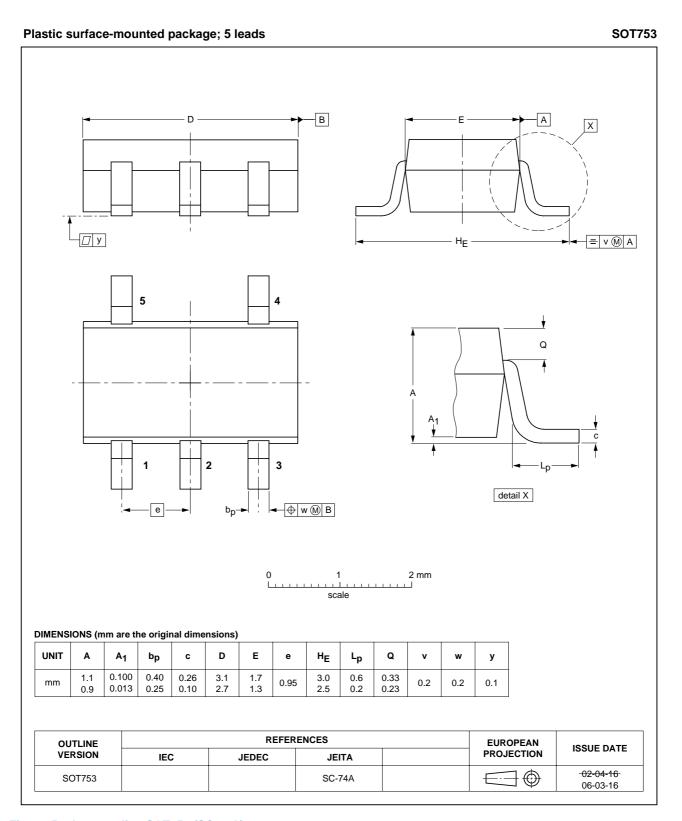


Fig 8. Package outline SOT753 (SC-74A)

# 14. Abbreviations

Table 9.	Abbreviations		
Acronym	Description		
DUT	Device Under Test		
TTL	Transistor-Transistor Logic		

# **15. Revision history**

#### Table 10.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT1G08_4	20070717	Product data sheet	-	74HC_HCT1G08_3
Modifications:		of this data sheet has been re of NXP Semiconductors.	edesigned to comply v	vith the new identity
	<ul> <li>Legal texts</li> </ul>	have been adapted to the new	w company name whe	ere appropriate.
	<ul> <li>Package S0</li> </ul>	OT353 changed to SOT353-1	in Table 1 and Figure	<u>7</u> .
	<ul> <li>Quick Refer</li> </ul>	rence Data and Soldering sec	tions removed.	
	<ul> <li>Section 2 "F</li> </ul>	Features" updated.		
74HC_HCT1G08_3	20020517	Product specification	-	74HC_HCT1G08_2
74HC_HCT1G08_2	20010302	Product specification	-	74HC_HCT1G08_1
74HC_HCT1G08_1	19981110	Preliminary specification	-	-

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Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[2] The term 'short data sheet' is explained in section "Definitions".

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### **NXP Semiconductors**

# 74HC1G08; 74HCT1G08

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